

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1184	(semiconductor with memory) and (bit adj line) and (word adj line) and transistor and resist\$4 and substrate and magnetic	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/08 11:05
L2	908	1 and (insulat\$3 or dielectric) and (cross\$3 or orthogonal\$3) and (gap or distan\$4 or spac\$3 or hole or open\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/08 10:52
L3	862	1 and (insulat\$3 or dielectric) and (cross\$3 or orthogonal\$3) and (gap or distan\$4 or space or hole or open\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/08 10:52
L5	102	3 and ((transistor or channel) with vertical\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/08 11:05
L6	99	5 and (second with (transistor or resist\$3 or bit or word))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/08 10:54
L7	17	((semiconductor with memory) and (bit adj line) and (word adj line) and transistor and resist\$4 and substrate and magnetic). clm.	US-PGPUB	OR	ON	2005/09/08 11:10
L8	12	365/97.ccls.	US-PGPUB	OR	ON	2005/09/08 11:26
L9	437	257/295.ccls.	US-PGPUB	OR	ON	2005/09/08 11:27
S2	143	matsuoka-hideyuki.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/13 13:11
S3	50	Ito-kenchi.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/13 13:11
S4	485	sakata-takeshi.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/13 13:12
S6	247	Itoh-Kiyoo.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/13 13:12
S7	787	S2 S3 S4 S6	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/13 13:13
S8	1	"20040105326"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/14 12:03
S9	143	matsuoka-hideyuki.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/14 12:03

S10	50	Ito-kenchi.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/14 12:03
S11	485	sakata-takeshi.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/14 12:03
S12	247	Itoh-Kiyoo.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/14 12:03
S13	787	S9 S10 S11 S12	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/14 12:03
S14	9	S13 and (megnet\$6 or ferromagnet\$5) and transistor	USPAT	OR	OFF	2005/04/14 14:21
S16	143	matsuoka-hideyuki.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/14 14:21
S17	50	Ito-kenchi.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/14 13:44
S18	485	sakata-takeshi.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/14 13:44
S19	247	Itoh-Kiyoo.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/14 13:44
S20	787	S16 S17 S18 S19	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/14 13:44
S21	1	"20040105326"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/14 13:44
S22	143	matsuoka-hideyuki.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/14 13:44
S23	50	Ito-kenchi.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/14 13:44
S24	485	sakata-takeshi.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/14 13:44

S25	247	Itoh-Kiyoo.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/14 13:44
S26	787	S22 S23 S24 S25	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/14 13:44
S27	9	S26 and (megnet\$6 or ferromagnet\$5) and transistor	USPAT	OR	OFF	2005/04/14 13:44
S28	1	"20020093845"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/14 14:21
S29	1	"20040105326"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/14 16:10
S30	1	"20040105326"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/15 11:34
S31	3	("6351408" "6359805" "6392924").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/04/15 15:06
S32	3	("6560135").URPN.	USPAT	OR	OFF	2005/04/15 16:11
S33	3	((magnet\$5 or ferromagnet\$5) near3 memory) and (vertical adj transistor) and (word adj line) and (substrate and (cross\$4 or perpendicula\$4 or orthogonal\$4))	USPAT	OR	OFF	2005/04/15 16:14
S34	8	((magnet\$5 or ferromagnet\$5) near3 memory) and (vertical adj transistor) and (word adj line) and (substrate and (cross\$4 or perpendicula\$4 or orthogonal\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/15 16:16
S35	5	S34 not S33	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/15 16:14
S36	23	((magnet\$5 or ferromagnet\$5)) and (vertical adj transistor) and (word adj line) and (substrate and (cross\$4 or perpendicula\$4 or orthogonal\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/15 16:27
S37	15	S36 not S34	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/15 16:17
S38	6	("4845533" "5032538" "5920788" "6087674" "6429449" "6437383").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/04/15 16:21
S39	3	((magnet\$5 or ferromagnet\$5)) and (vertical adj transistor) and (soft adj magnet\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/15 16:33
S40	3	(vertical adj transistor) and (soft adj magnet\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/15 16:33

S41	9	(vertical adj transistor) and ("NiFe")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/15 16:37
S42	6	S41 not (S31 S32 S33 S34 S36)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/15 16:38
S43	63	(vertical near3 transistor) and ("NiFe" or (soft adj magnet\$4 or ferromagnet\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/15 16:38
S44	51	S43 not (S31 S32 S33 S34 S36 S41)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/15 18:29
S45	20	S44 and substrate and (word adj line) and memory	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/15 17:13
S46	31	S44 not S45	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/15 18:27
S47	0	(vetical\$3 near2 transistor) and (((magnetic\$4 or ferromagnetic\$4 or ferroelectri\$5) near soft) or "NiFe")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/15 18:29
S48	15	(vertical\$3 near2 transistor) and (((magnetic\$4 or ferromagnetic\$4 or ferroelectri\$5) near soft) or "NiFe")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/15 18:32
S50	2	S48 not (S31 S32 S33 S34 S36 S41 S46)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/09/08 10:48
S51	180	transistor and ((bit or data) adj line) same (((magnetic\$4 or ferromagnetic\$4 or ferroelectri\$5) near soft) or "NiFe")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/15 18:33
S52	189	transistor and ((bit or data) adj line) same (soft near2 ((magnetic\$4 or ferromagnetic\$4 or ferroelectri\$5)) or "NiFe")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/15 18:33
S53	183	S52 not (S31 S32 S33 S34 S36 S41 S46)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/15 18:34
S54	7	S53 and (vertical\$3 same transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/15 18:35